

2N6034 2N6035 2N6036 PNP
2N6037 2N6038 2N6039 NPN

**COMPLEMENTARY SILICON
DARLINGTON POWER
TRANSISTORS**



TO-18 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6034, 2N6037 series devices are complementary silicon Darlington power transistors, manufactured by the epitaxial base process, designed for general purpose amplifier and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)		2N6034	2N6035	2N6036	UNITS
SYMBOL	2N6037	2N6038	2N6039		
Collector-Base Voltage	V_{CB0}	40	60	80	V
Collector-Emitter Voltage	V_{CEO}	40	60	80	V
Emitter-Base Voltage	V_{EBO}		5.0		V
Continuous Collector Current	I_C		4.0		A
Peak Collector Current	I_{CM}		8.0		A
Continuous Base Current	I_B		100		mA
Power Dissipation	P_D		40		W
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D		1.5		W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JA}		83.3		$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}		3.12		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)		MIN	MAX	UNITS
SYMBOL	TEST CONDITIONS			
I_{CBO}	$V_{CB}=\text{Rated } V_{CB0}$		500	μA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{BE}=1.5\text{V}$		100	μA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{BE}=1.5\text{V}, T_C=125^\circ\text{C}$		500	μA
I_{CEO}	$V_{CE}=\text{Rated } V_{CEO}$		100	μA
I_{EBO}	$V_{EB}=5.0\text{V}$		2.0	mA
BV_{CEO}	$I_C=100\text{mA}$ (2N6034, 2N6037)	40		V
BV_{CEO}	$I_C=100\text{mA}$ (2N6035, 2N6038)	60		V
BV_{CEO}	$I_C=100\text{mA}$ (2N6036, 2N6039)	80		V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=8.0\text{mA}$		2.0	V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=40\text{mA}$		3.0	V
$V_{BE(SAT)}$	$I_C=4.0\text{A}, I_B=40\text{mA}$		4.0	V
$V_{BE(ON)}$	$V_{CE}=3.0\text{V}, I_C=2.0\text{A}$		2.8	V
h_{FE}	$V_{CE}=3.0\text{V}, I_C=500\text{mA}$	500		
h_{FE}	$V_{CE}=3.0\text{V}, I_C=2.0\text{A}$	750	15K	
h_{FE}	$V_{CE}=3.0\text{V}, I_C=4.0\text{A}$	100		
f_T	$V_{CE}=10\text{V}, I_C=750\text{mA}, f=1.0\text{MHz}$	25		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (PNP)		200	pF
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (NPN)		100	pF

R1 (12-March 2014)

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TO-126 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Emitter
- 2) Collector
- 3) Base

MARKING:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.094	0.110	2.40	2.80
B	0.050		1.27	
C	0.015	0.030	0.38	0.75
D	0.291	0.335	7.40	8.50
E	0.148		3.75	
F	0.118	0.134	3.00	3.40
G	0.413	0.472	10.50	12.00
H	0.618		15.70	
J	0.024	0.035	0.62	0.90
K	0.089		2.25	
L	0.177		4.50	
M	0.045	0.055	1.14	1.40
N	0.083		2.10	

TO-126 (REV:R3)

R1 (12-March 2014)